

**SOT-23** 

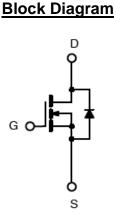
#### Pin Definition: 1. Gate

1. Gate 2. Source	Parameter		Value	Unit	
3. Drain	V <sub>DS</sub>		30	V	
Note: MSL 1 (Moisture Sensitivity Level) per J-STD-020	R <sub>DS(on)</sub> (max)	$V_{GS} = 10V$	24		
		$V_{GS} = 4.5V$	34	mΩ	
Qg			4.1	nC	

### **Ordering Information**

Ordering code	Package	Packing
TSM240N03CX RFG	SOT-23	3kpcs / 7" Reel

Note: Halogen-free according to IEC 61249-2-21 definition •



N-Channel MOSFET

#### Absolute Maximum Ratings (T<sub>c</sub> = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V <sub>DS</sub>	30	V
Gate-Source Voltage		V <sub>GS</sub>	±20	V
Continuous Drain Current	$T_{C} = 25^{\circ}C$	- I <sub>D</sub>	6.5	А
	$T_{c} = 100^{\circ}C$		4.1	А
Pulsed Drain Current (Note 1)		I <sub>DM</sub>	26	А
Single Pulse Avalanche Energy (Note 2)		E <sub>AS</sub>	32	mJ
Power Dissipation @ $T_c = 25^{\circ}C$		P <sub>D</sub>	1.56	W
Operating Junction Temperature		TJ	150	°C
Storage Temperature Range		T <sub>STG</sub>	-55 to +150	°C

#### **Thermal Performance**

Parameter	Symbol	Limit	Unit	
Thermal Resistance - Junction to Ambient	$R_{\Theta JA}$	80	°C/W	

**Key Parameter Performance** 

# **TSM240N03CX 30V N-Channel Power MOSFET**





#### Electrical Specifications (T<sub>c</sub> = 25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250 \mu A$	BV <sub>DSS</sub>	30			V
	$V_{GS} = 10V, I_D = 6A$	R <sub>DS(on)</sub>		17	24	mΩ
Drain-Source On-State Resistance	$V_{GS} = 4.5V, I_D = 4A$			22	34	
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	V <sub>GS(TH)</sub>	1.2	1.4	2.5	V
	$V_{DS} = 30V, V_{GS} = 0V$				1	μA
Zero Gate Voltage Drain Current	V <sub>DS</sub> = 24V, T <sub>J</sub> = 125°C	I <sub>DSS</sub>			10	
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I <sub>GSS</sub>			±100	μA
Forward Transconductance (Note 3)	$V_{DS} = 10V, I_{D} = 4A$	<b>g</b> <sub>fs</sub>		6.5		S
Dynamic				1	•	
Total Gate Charge (Note 3,4)		Qg		4.1		nC
Gate-Source Charge (Note 3,4)	$V_{DS} = 15V, I_D = 6A,$	Q <sub>gs</sub>		1		
Gate-Drain Charge (Note 3,4)	$V_{GS} = 4.5V$	Q <sub>gd</sub>		2.1		
Input Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$	C <sub>iss</sub>		345		
Output Capacitance		C <sub>oss</sub>		55		pF
Reverse Transfer Capacitance	f = 1.0MHz	C <sub>rss</sub>		32		
Switching	1				•	
Turn-On Delay Time (Note 3,4)		t <sub>d(on)</sub>		2.8		
Turn-On Rise Time (Note 3,4)	V <sub>DD</sub> = 15V, I <sub>D</sub> = 1A,	t <sub>r</sub>		7.2		
Turn-Off Delay Time (Note 3,4)	$V_{GS} = 10V, R_G = 6\Omega$	t <sub>d(off)</sub>		15.8		ns
Turn-Off Fall Time (Note 3,4)		t <sub>f</sub>		4.6		
Source-Drain Diode Ratings and Ch	aracteristic			1		
Maximum Continuous Drain-Source	Integral reverse diode in the MOSFET	I			6.5	٨
Diode Forward Current		۱ <sub>s</sub>			0.5	A
Maximum Pulse Drain-Source Diode		I <sub>SM</sub>			26	А
Forward Current		_				
Diode-Source Forward Voltage	$V_{GS} = 0V, I_{S} = 1A$	$V_{SD}$			1	V

Note:

1. Pulse width limited by safe operating area

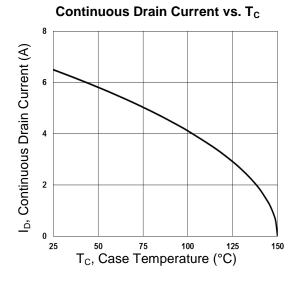
2. L = 1mH,  $I_{AS}$  = 8A,  $V_{DD}$  = 25V,  $R_G$  = 25 $\Omega$ , Starting  $T_J$  = 25°C

3. Pulse test: pulse width  $\leq$  300µs, duty cycle  $\leq$  2%

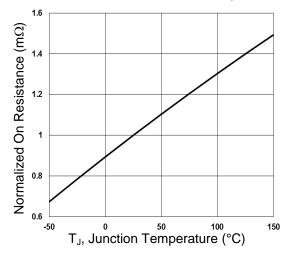
4. Switching time is essentially independent of operating temperature.



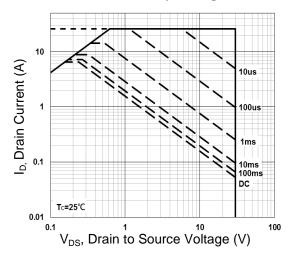
#### **Electrical Characteristics Curve**

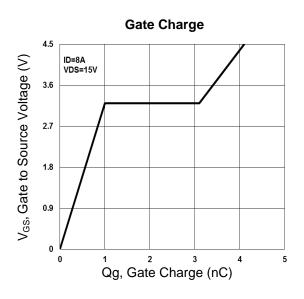


**On-Resistance vs. Junction Temperature** 

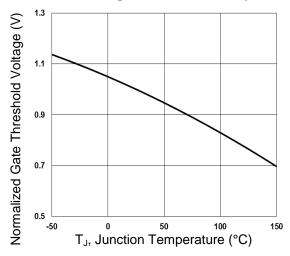


Maximum Safe Operating Area

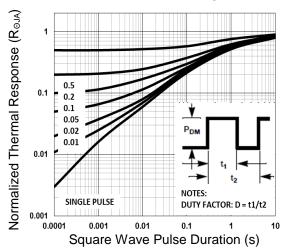




**Threshold Voltage vs. Junction Temperature** 

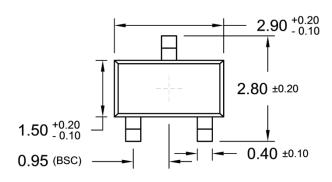


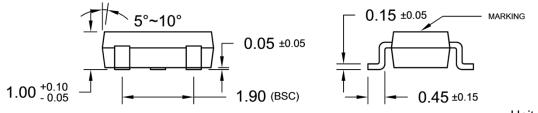
Normalized Thermal Transient Impedance Curve





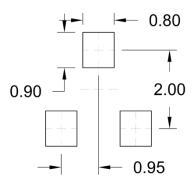
# SOT-23 Mechanical Drawing





**Unit: Millimeters** 

## SUGGESTED PAD LAYOUT (Unit: Millimeters)



### **Marking Diagram**



- 24 = Device Code
- Y = Year Code
- M = Month Code for Halogen Free Product
  (O=Jan, P=Feb, Q=Mar, R=Apl, S=May, T=Jun, U=Jul, V=Aug, W=Sep, X=Oct, Y=Nov, Z=Dec)
- L = Lot Code





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